



XA-9947

PATENT APPLICATION

IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Nobuyuki SUGII et al.

Appln. No.: 10/673,789

Group Art Unit: 2811

Filed: September 30, 2003

For: Insulated-Gate Field-Effect Transistor, Method of
Fabricating the Same, and Semiconductor Device
Employing Same

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Prior to examination, please amend the above-
identified patent application as indicated below.

Amendments to the Specification begin on page 2 of
this paper.

Amendments to the Claims are reflected in the listing
of claims which begins on page 3 of this paper.

Remarks begin on page 14 of this paper.